



## FEATURES

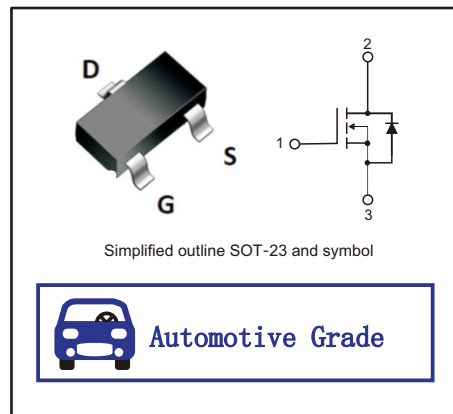
- $R_{DS(ON)} \leq 140m\Omega @ V_{GS} = 10V$
- $R_{DS(ON)} \leq 170m\Omega @ V_{GS} = 4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- Capable doing Cu wire bonding
- Qualified to AEC-Q101 Standards for High Reliability

## APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Load Switch
- DSC

## PINNING

PIN	DESCRIPTION
1	GATE
2	DRAIN
3	SOURCE



## MAXIMUM RATINGS (Ta =25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	60	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Continuous Drain Current@ $T_A = 25^\circ C$	$I_D$	1.9	A
Continuous Drain Current@ $T_A = 75^\circ C$		1.2	A
Pulsed Drain Current	$I_{DM}$	8	A
Power Dissipation	$P_D$	0.7	W
Operation Junction Temperature	$T_j$	150	$^\circ C$

Tip: The device mounted on 1in<sup>2</sup> Fr4 board with 2 oz copper



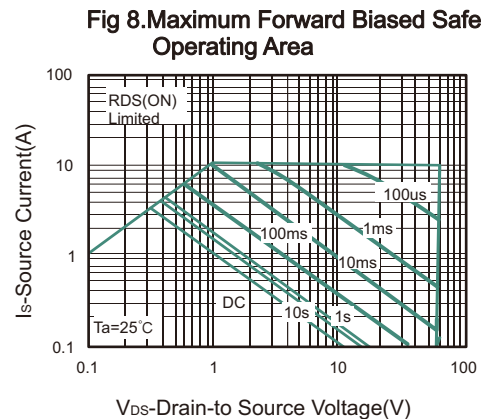
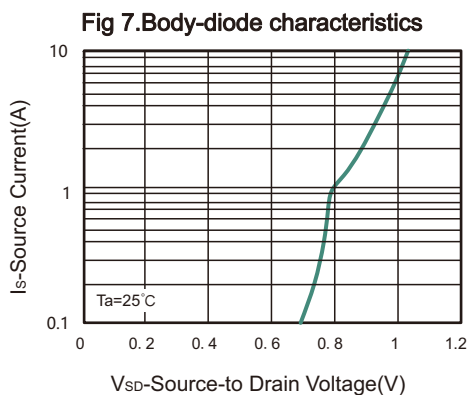
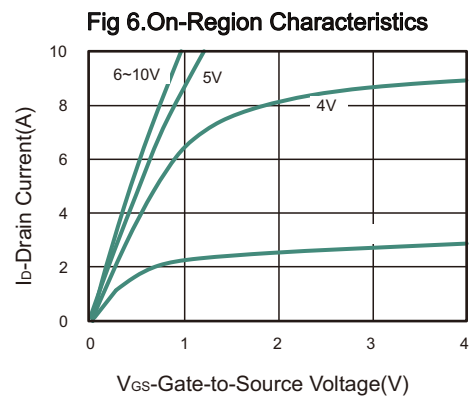
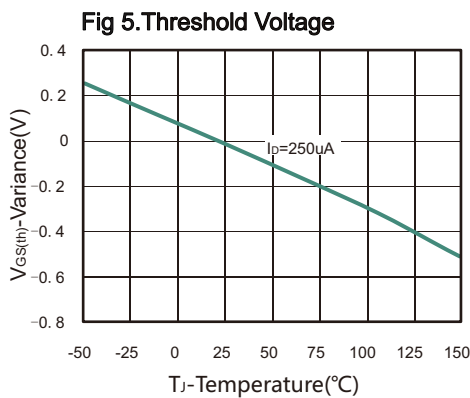
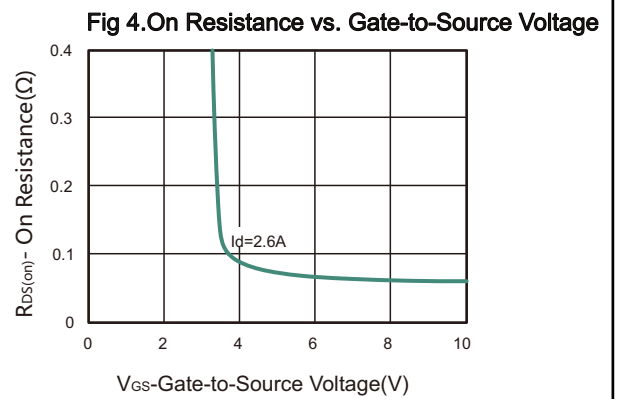
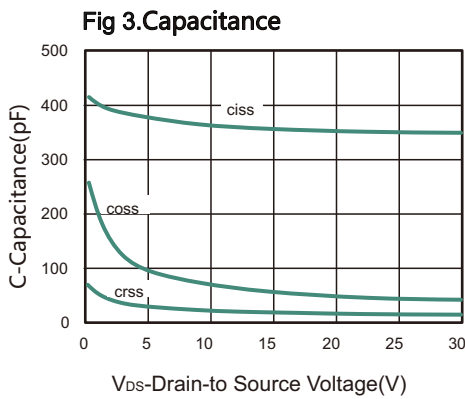
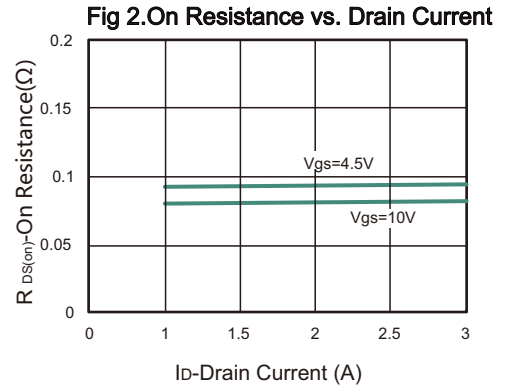
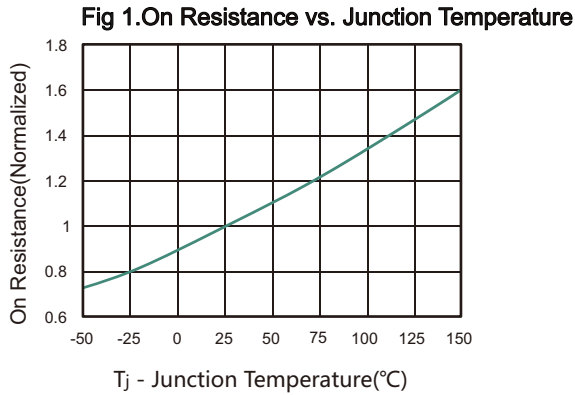
ELECTRICAL CHARACTERISTICS (Ta = 25°C unless otherwise noted. )

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
OFF Characteristics						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 60V, V_{GS} = 0V$			1	$\mu A$
Gate- Source Leakage Current	Forward	$V_{GS} = 20V, V_{DS} = 0V$			100	nA
	Reverse	$V_{GS} = -20V, V_{DS} = 0V$			-100	
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1		3	V
Static Drain-Source On-State Resistance <sup>1</sup> .	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 2.6A$		102	140	m $\Omega$
		$V_{GS} = 4.5V, I_D = 2.1A$		125	170	
Dynamic Characteristics						
Input Capacitance	$C_{ISS}$	$V_{DS} = 30V$ $V_{GS} = 0V$ $f = 1.0MHz$		350		pF
Output Capacitance	$C_{OSS}$			40		
Reverse Transfer Capacitance	$C_{RSS}$			12		
Switching Characteristics						
Total Gate Charge	$Q_g$	$V_{DS} = 30V$ $V_{GS} = 4.5V$ $I_D = 2.6A$		6.5		nC
Gate-Source Charge	$Q_{gs}$			2.2		
Gate-Drain Charge	$Q_{gd}$			2.7		
Switching Characteristics						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 20V,$ $R_L = 20\Omega,$ $V_{GEN} = 10V,$ $I_D = 1A,$ $R_D = 1\Omega$		10		ns
Turn-On Rise Time	$t_{rr}$			11		
Turn-Off Delay Time	$t_{d(off)}$			29		
Turn-Off Fall Time	$t_f$			3		

Notes1: Pulse test: pulse width 300us, duty cycle  $\leq 2\%$ , Guaranteed by design, not subject to production testing.



## Typical Performance Characteristics





### Typical Performance Characteristics

Fig 9. Single Pulse Maximum Power Dissipation

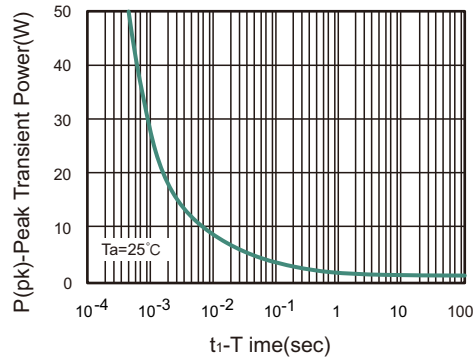
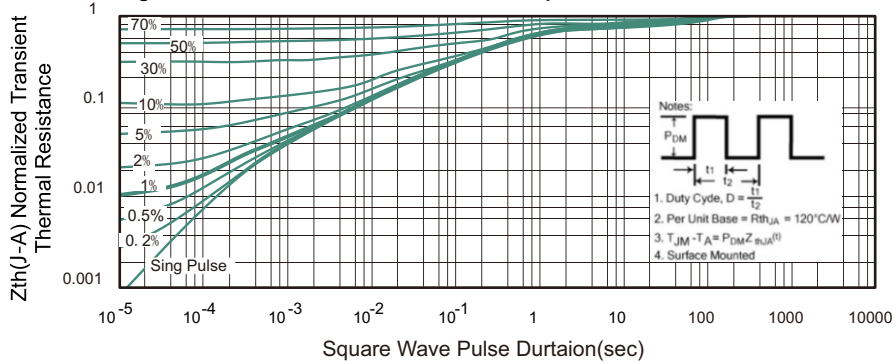
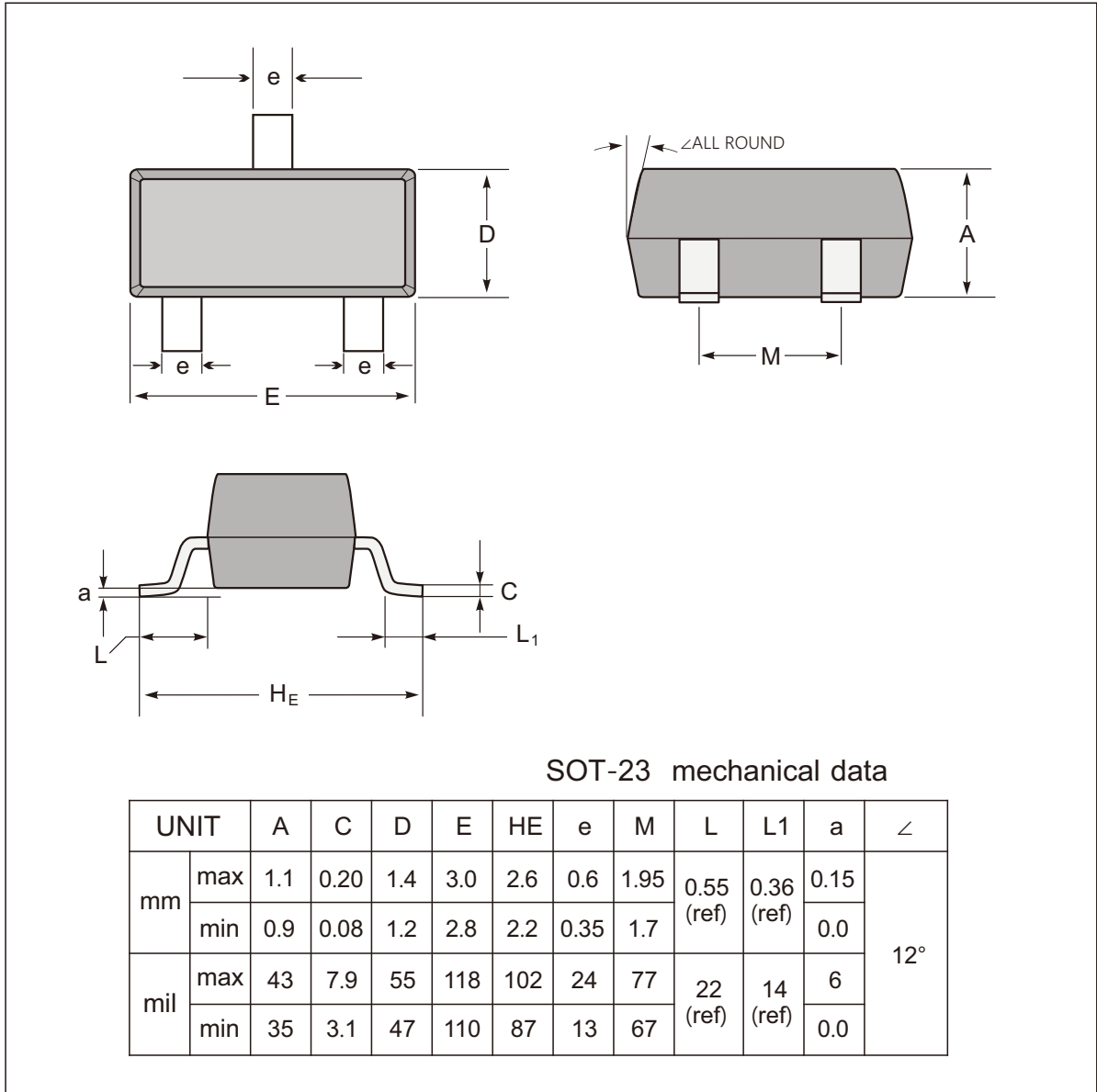


Fig 10. Normalized Thermal Transient Impedance, Junction-Ambient

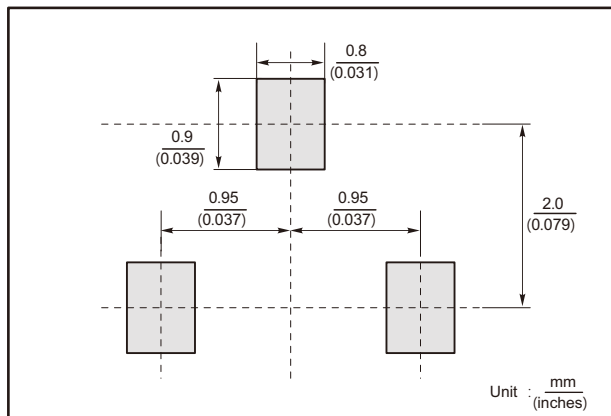




### SOT-23 Package Outline Dimensions



#### The recommended mounting pad size



#### Marking

Type number	Marking code
NM2308WD	2308



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